

AMENDMENTS TO THE CLAIMS:

Claims 1-4 (cancelled)

5. (Currently amended) A plating method comprising:
providing a substrate having fine trench patterns which are covered with a seed layer;
disposing said substrate adjacent an anode such that said substrate and said anode face one another and define a plating space therebetween;
disposing a plating liquid impregnation material, comprising a porous ceramic, in said plating space such that a gap is formed between said substrate and said plating liquid impregnation material;
supplying a plating liquid into said plating space; and
forming a plated film on a surface of said seed layer by
(i) applying an electric current between said substrate and said anode without bringing said substrate into contact with said plating liquid impregnation material, and
(ii) moving a portion of said substrate facing said plating liquid impregnation material, relative to said anode, in such a manner that an inner central portion of the surface of said seed layer faces said plating liquid impregnation material for a longer period of time than does an outer peripheral portion of the surface of said seed layer.

6. (Previously presented) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by rotating said substrate.

7. (Previously presented) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by rotating said anode.

8. (Previously presented) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by translating said anode.

9. (New) The plating method according to claim 5, wherein

disposing a plating liquid impregnation material in said plating space such that a gap is formed between said substrate and said plating liquid impregnation material comprises disposing said plating liquid impregnation material in said plating space such that a gap of from 0.5 mm to 3.0 mm is formed between said substrate and said plating liquid impregnation material.

10. (New) The plating method according to claim 5, wherein forming a plated film on a surface of said seed layer comprises forming, in an apparatus, said plated film on said surface of said seed layer, said method further comprising:

in said apparatus, rinsing said substrate with water after completing formation of said plated film.

11. (New) The plating method according to claim 5, wherein forming a plated film on a surface of said seed layer comprises forming, in an apparatus, said plated film on said surface of said seed layer, while said substrate is held by a substrate holder, said method further comprising:

in said apparatus, washing said substrate and said substrate holder after completing formation of said plated film.

12. (New) The plating method according to claim 11, further comprising:

in said apparatus, drying said substrate after the washing of said substrate.